

DATA SHEET

PDTA143E series

PNP resistor-equipped transistors;

$R1 = 4.7\text{ k}\Omega$, $R2 = 4.7\text{ k}\Omega$

Product data sheet
Supersedes data of 2003 Sep 08

2004 Aug 04

PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

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FEATURES

- Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

APPLICATIONS

- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

QUICK REFERENCE DATA

| SYMBOL | PARAMETER | TYP. | MAX. | UNIT |
|------------------|---------------------------|------|------|------------|
| V _{CEO} | collector-emitter voltage | – | –50 | V |
| I _O | output current (DC) | – | –100 | mA |
| R1 | bias resistor | 4.7 | – | k Ω |
| R2 | bias resistor | 4.7 | – | k Ω |

DESCRIPTION

PNP resistor-equipped transistor (see “Simplified outline, symbol and pinning” for package details).

PRODUCT OVERVIEW

| TYPE NUMBER | PACKAGE | | MARKING CODE | NPN COMPLEMENT |
|-------------|---------------|--------|--------------------|----------------|
| | PHILIPS | EIAJ | | |
| PDTA143EE | SOT416 | SC-75 | 01 | PDTC143EE |
| PDTA143EEF | SOT490 | SC-89 | 50 | PDTC143EEF |
| PDTA143EK | SOT346 | SC-59 | 01 | PDTC143EK |
| PDTA143EM | SOT883 | SC-101 | DL | PDTC143EM |
| PDTA143ES | SOT54 (TO-92) | SC-43 | TA143E | PDTC143ES |
| PDTA143ET | SOT23 | – | *01 ⁽¹⁾ | PDTC143ET |
| PDTA143EU | SOT323 | SC-70 | *01 ⁽¹⁾ | PDTC143EU |

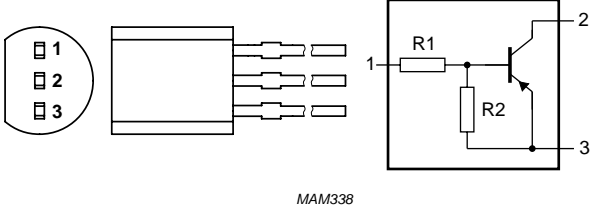
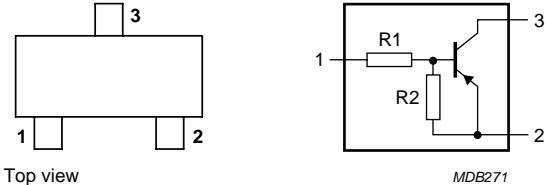
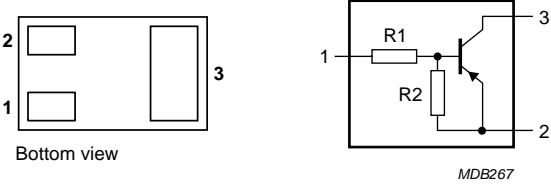
Note

- * = p: Made in Hong Kong.
* = t: Made in Malaysia.
* = W: Made in China.

PNP resistor-equipped transistors;
R1 = 4.7 kΩ, R2 = 4.7 kΩ

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SIMPLIFIED OUTLINE, SYMBOL AND PINNING

| TYPE NUMBER | SIMPLIFIED OUTLINE AND SYMBOL | PINNING | |
|--|--|-------------|------------------------------|
| | | PIN | DESCRIPTION |
| PDTA143ES |  | 1 2 3 | base collector emitter |
| PDTA143EE PDTA143EEF PDTA143EK PDTA143ET PDTA143EU |  | 1 2 3 | base emitter collector |
| PDTA143EM |  | 1 2 3 | base emitter collector |

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|------------------|-------------------------------|--------------------------|------|------|------|
| V _{CBO} | collector-base voltage | open emitter | – | –50 | V |
| V _{CEO} | collector-emitter voltage | open base | – | –50 | V |
| V _{EBO} | emitter-base voltage | open collector | – | –10 | V |
| V _I | input voltage | | | | |
| | positive | | – | +10 | V |
| | negative | | – | –30 | V |
| I _O | output current (DC) | | – | –100 | mA |
| I _{CM} | peak collector current | | – | –100 | mA |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | | | |
| | SOT23 | note 1 | – | 250 | mW |
| | SOT54 | note 1 | – | 500 | mW |
| | SOT323 | note 1 | – | 200 | mW |
| | SOT346 | note 1 | – | 250 | mW |
| | SOT416 | note 1 | – | 150 | mW |
| | SOT490 | notes 1 and 2 | – | 250 | mW |
| | SOT883 | notes 2 and 3 | – | 250 | mW |
| T _{stg} | storage temperature | | –65 | +150 | °C |
| T _j | junction temperature | | – | 150 | °C |
| T _{amb} | operating ambient temperature | | –65 | +150 | °C |

Notes

1. Refer to standard mounting conditions.
2. Reflow soldering is the only recommended soldering method.
3. Refer to SOT883 standard mounting conditions; FR4 with 60 μ m copper strip line.

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|---------------------|---|---------------|-------|------|
| R _{th j-a} | thermal resistance from junction to ambient | in free air | | |
| | SOT23 | note 1 | 500 | K/W |
| | SOT54 | note 1 | 250 | K/W |
| | SOT323 | note 1 | 625 | K/W |
| | SOT346 | note 1 | 500 | K/W |
| | SOT416 | note 1 | 833 | K/W |
| | SOT490 | notes 1 and 2 | 500 | K/W |
| | SOT883 | notes 2 and 3 | 500 | K/W |

Notes

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2. Reflow soldering is the only recommended soldering method.
3. Refer to SOT883 standard mounting conditions; FR4 with 60 μ m copper strip line.

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R1 = 4.7 k Ω , R2 = 4.7 k Ω

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CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|---------------------|--------------------------------------|---|------|------|------|------------|
| I _{CBO} | collector-base cut-off current | V _{CB} = -50 V; I _E = 0 | – | – | -100 | nA |
| I _{CEO} | collector-emitter cut-off current | V _{CE} = -30 V; I _B = 0 | – | – | -1 | μ A |
| | | V _{CE} = -30 V; I _B = 0; T _j = 150 °C | – | – | -50 | μ A |
| I _{EBO} | emitter-base cut-off current | V _{EB} = -5 V; I _C = 0 | – | – | -0.9 | mA |
| h _{FE} | DC current gain | V _{CE} = -5 V; I _C = -10 mA | 30 | – | – | |
| V _{CEsat} | collector-emitter saturation voltage | I _C = -10 mA; I _B = -0.5 mA | – | – | -150 | mV |
| V _{i(off)} | input-off voltage | I _C = -100 μ A; V _{CE} = -5 V | – | -1.1 | -0.5 | V |
| V _{i(on)} | input-on voltage | I _C = -20 mA; V _{CE} = -0.3 V | -2.5 | -1.9 | – | V |
| R1 | input resistor | | 3.3 | 4.7 | 6.1 | k Ω |
| $\frac{R2}{R1}$ | resistor ratio | | 0.8 | 1 | 1.2 | |
| C _c | collector capacitance | I _E = i _e = 0; V _{CB} = -10 V; f = 1 MHz | – | – | 3 | pF |

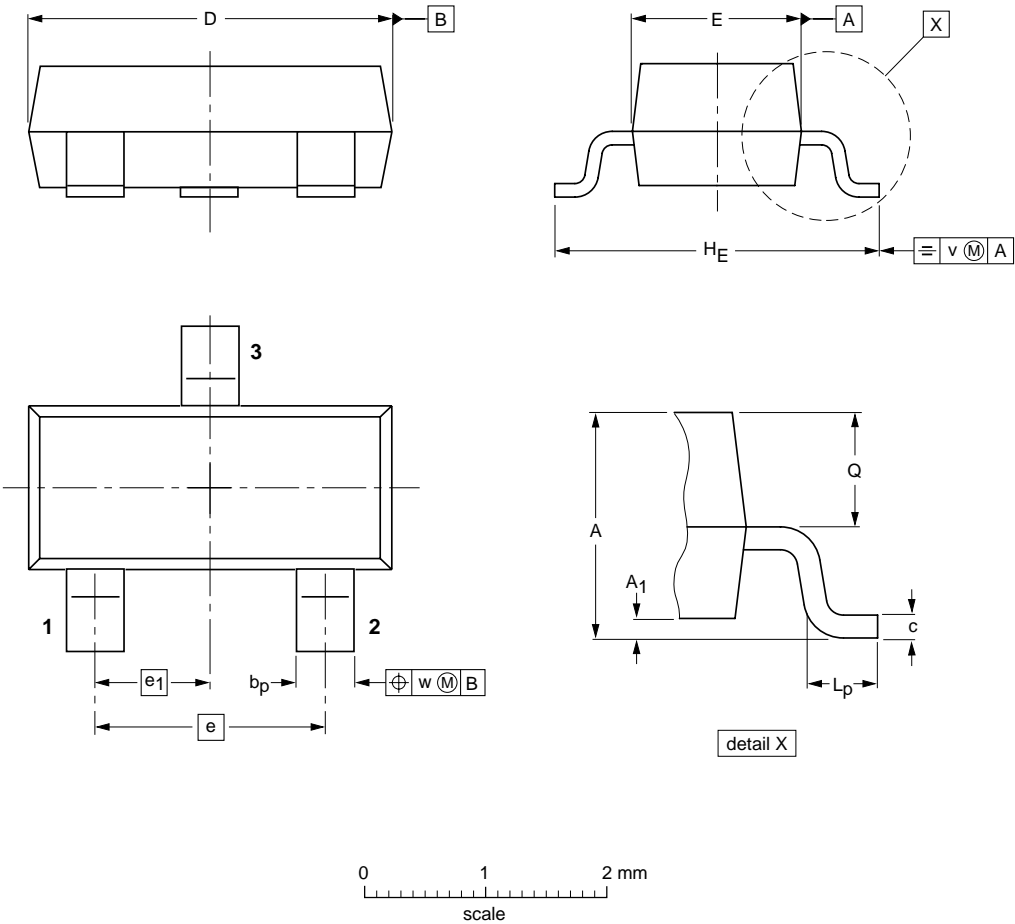
PNP resistor-equipped transistors;
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PDTA143E series

PACKAGE OUTLINES


Plastic surface-mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

| UNIT | A | A ₁ max. | b _p | c | D | E | e | e ₁ | H _E | L _p | Q | v | w |
|------|------------|------------------------|----------------|--------------|------------|------------|-----|----------------|----------------|----------------|--------------|-----|-----|
| mm | 1.1 0.9 | 0.1 | 0.48 0.38 | 0.15 0.09 | 3.0 2.8 | 1.4 1.2 | 1.9 | 0.95 | 2.5 2.1 | 0.45 0.15 | 0.55 0.45 | 0.2 | 0.1 |

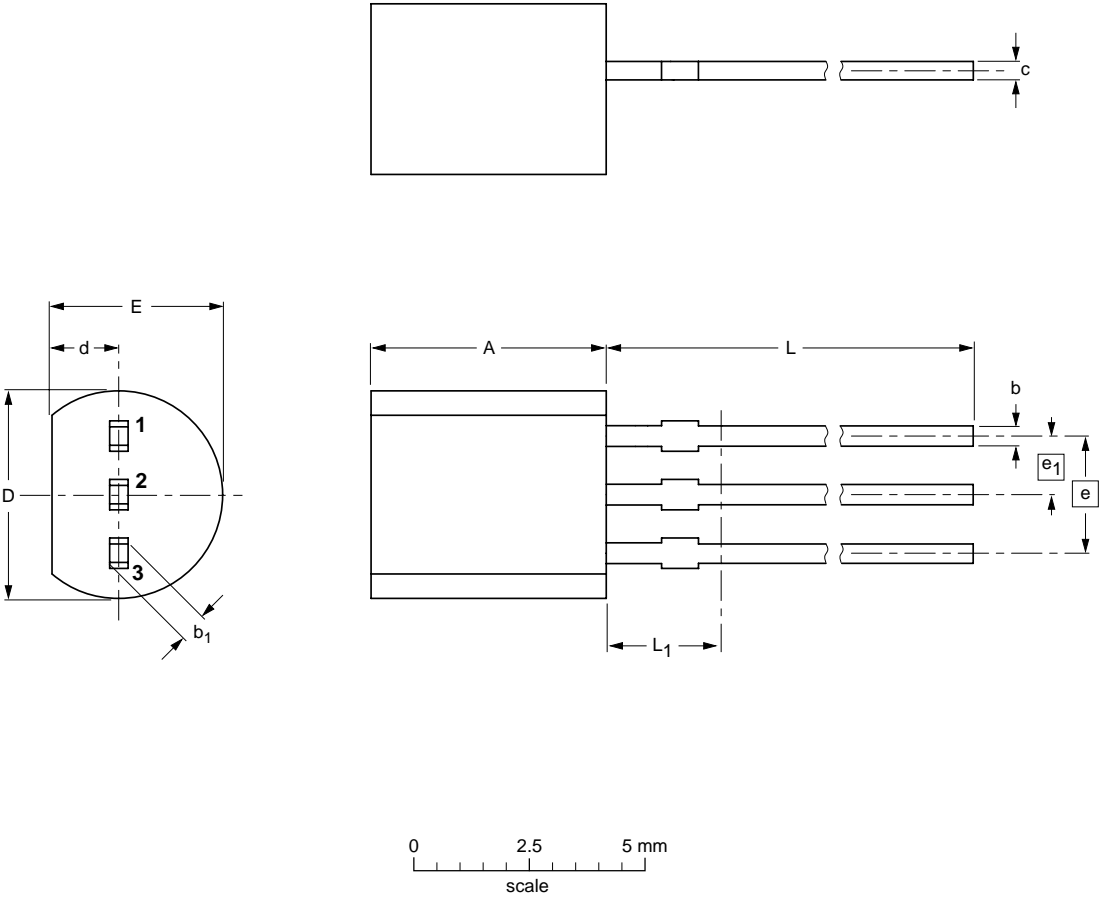
| OUTLINE VERSION | REFERENCES | | | | EUROPEAN PROJECTION | ISSUE DATE |
|--------------------|------------|----------|-------|--|---|----------------------|
| | IEC | JEDEC | JEITA | | | |
| SOT23 | | TO-236AB | | |  | 04-11-04 06-03-16 |

PNP resistor-equipped transistors;
R1 = 4.7 kΩ, R2 = 4.7 kΩ

PDTA143E series

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



DIMENSIONS (mm are the original dimensions)

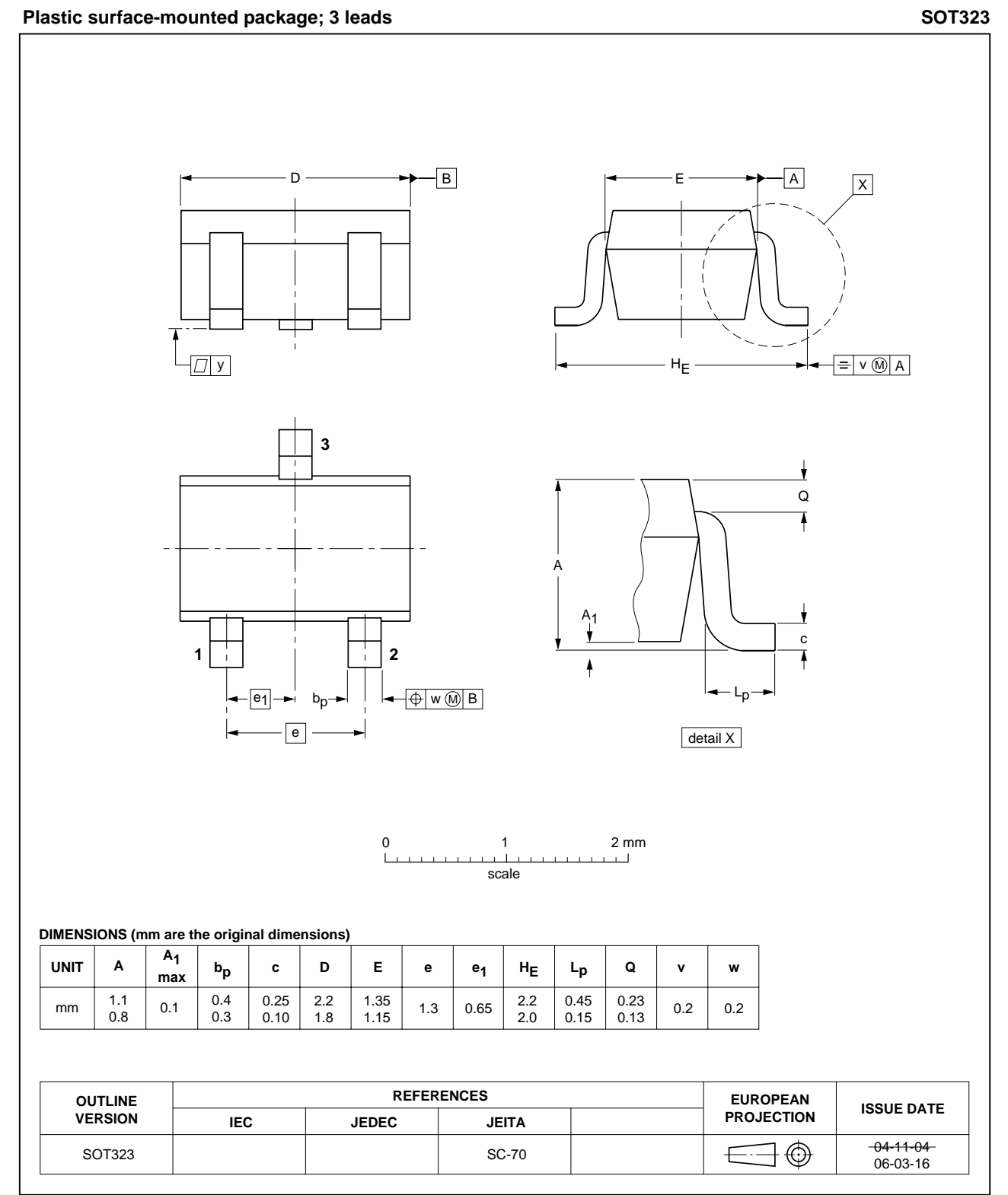
| UNIT | A | b | b ₁ | c | D | d | E | e | e ₁ | L | L ₁ ⁽¹⁾ max. |
|------|------------|--------------|----------------|--------------|------------|------------|------------|------|----------------|--------------|---------------------------------------|
| mm | 5.2 5.0 | 0.48 0.40 | 0.66 0.55 | 0.45 0.38 | 4.8 4.4 | 1.7 1.4 | 4.2 3.6 | 2.54 | 1.27 | 14.5 12.7 | 2.5 |

Note
1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

| OUTLINE VERSION | REFERENCES | | | | EUROPEAN PROJECTION | ISSUE DATE |
|--------------------|------------|-------|--------|--|------------------------|----------------------|
| | IEC | JEDEC | JEITA | | | |
| SOT54 | | TO-92 | SC-43A | | | 04-06-28 04-11-16 |

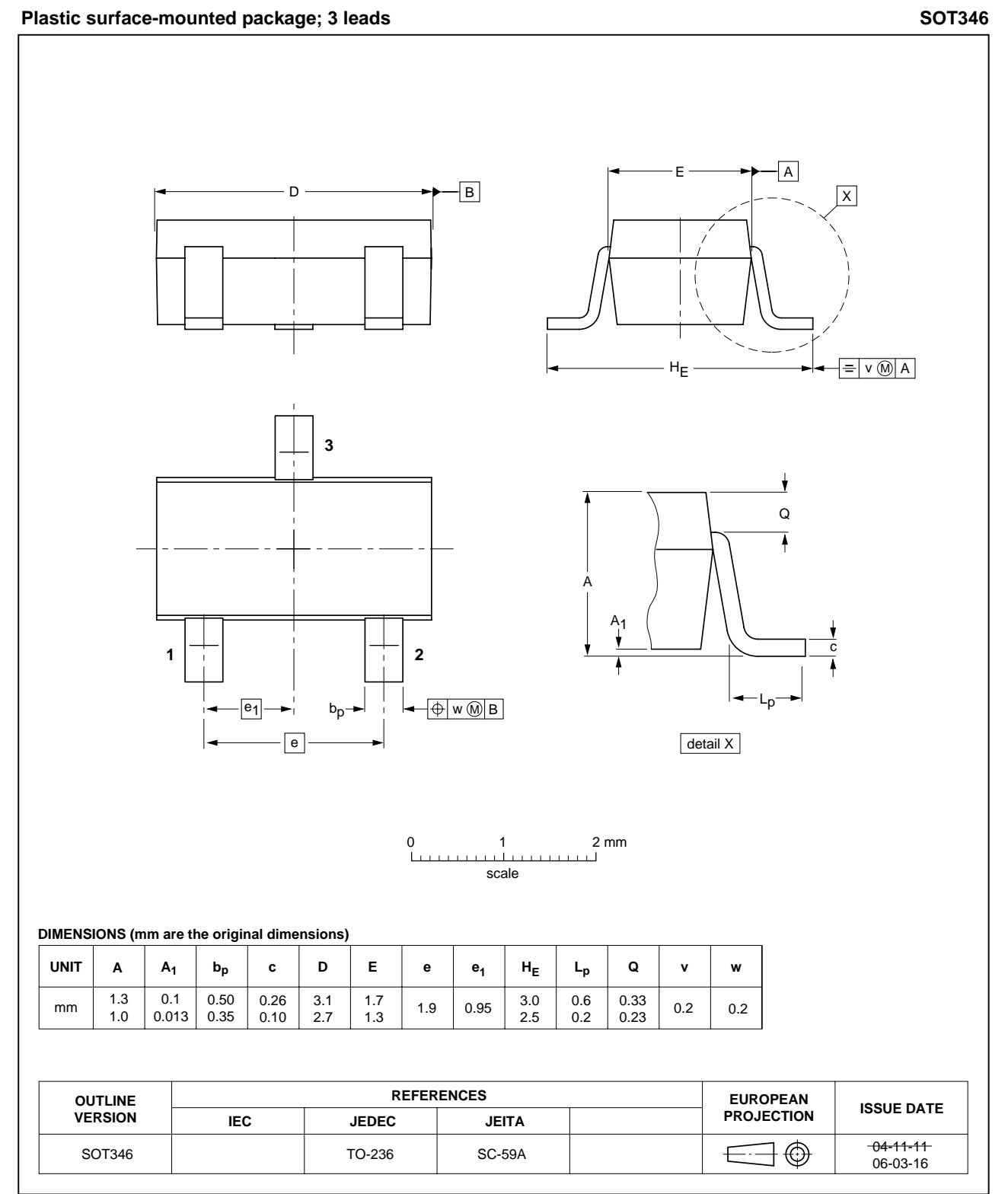
PNP resistor-equipped transistors;
R1 = 4.7 kΩ, R2 = 4.7 kΩ

PDTA143E series



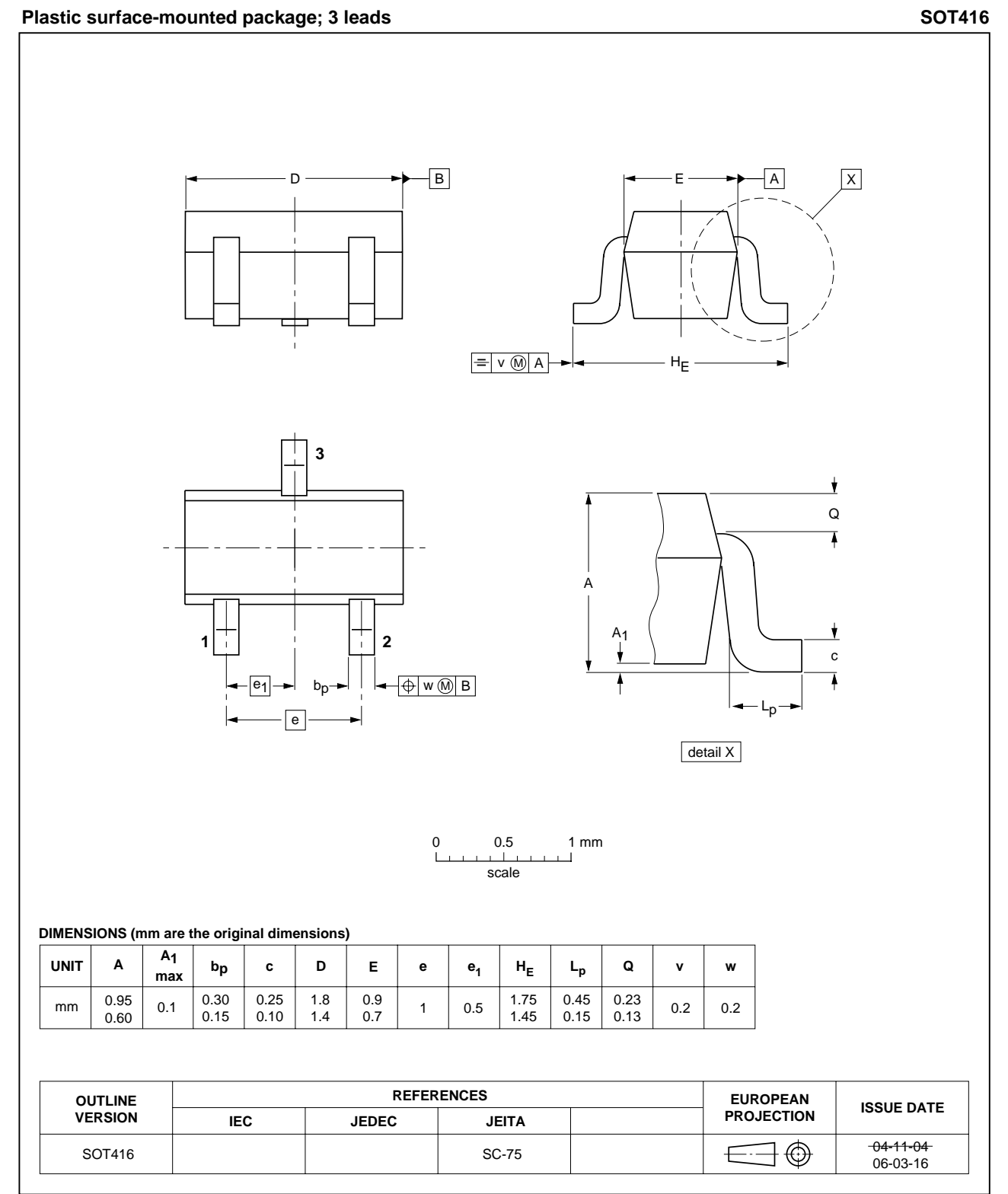
PNP resistor-equipped transistors;
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PDTA143E series



PNP resistor-equipped transistors;
R1 = 4.7 kΩ, R2 = 4.7 kΩ

PDTA143E series

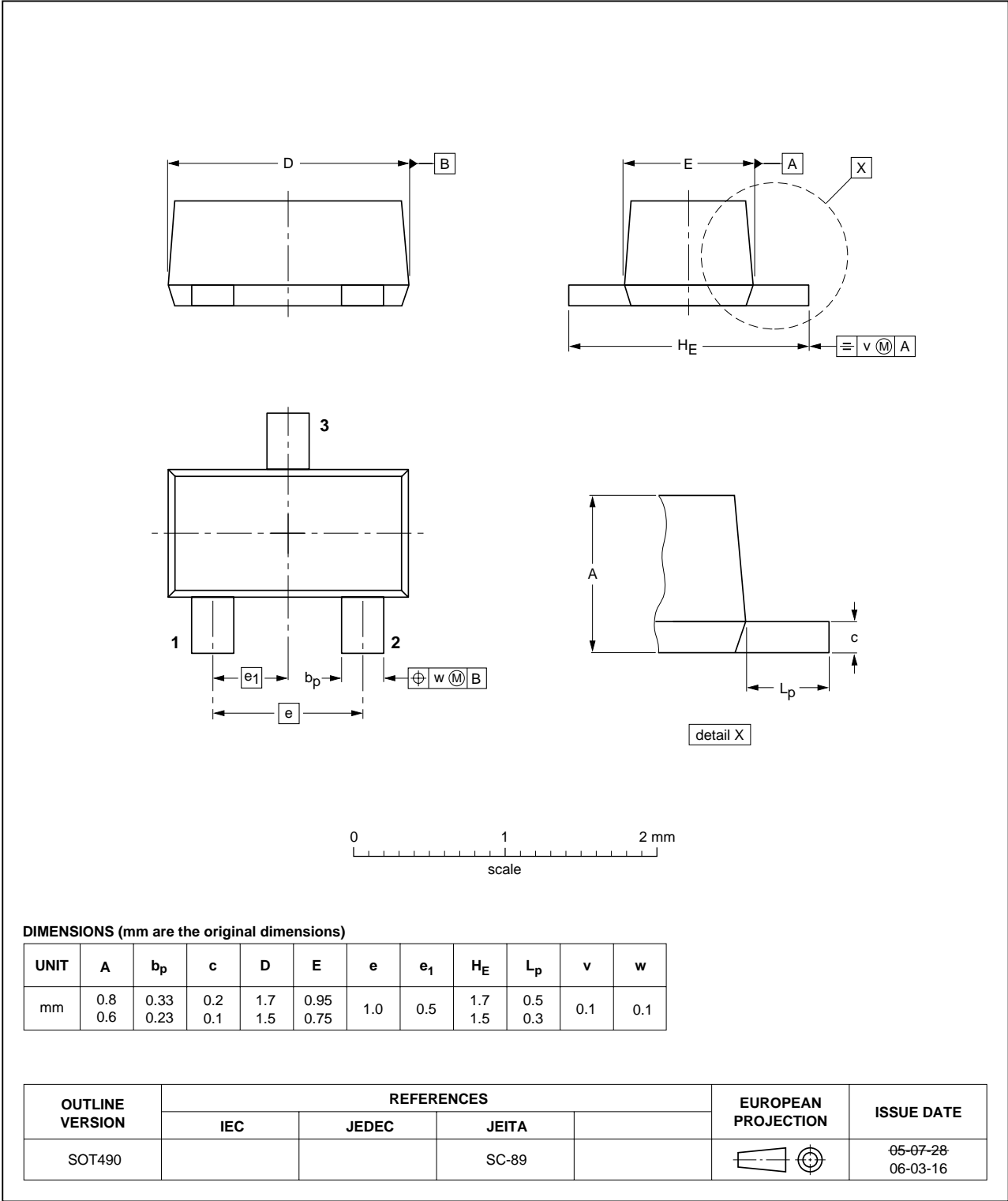


PNP resistor-equipped transistors;
R1 = 4.7 kΩ, R2 = 4.7 kΩ

PDTA143E series

Plastic surface-mounted package; 3 leads

SOT490

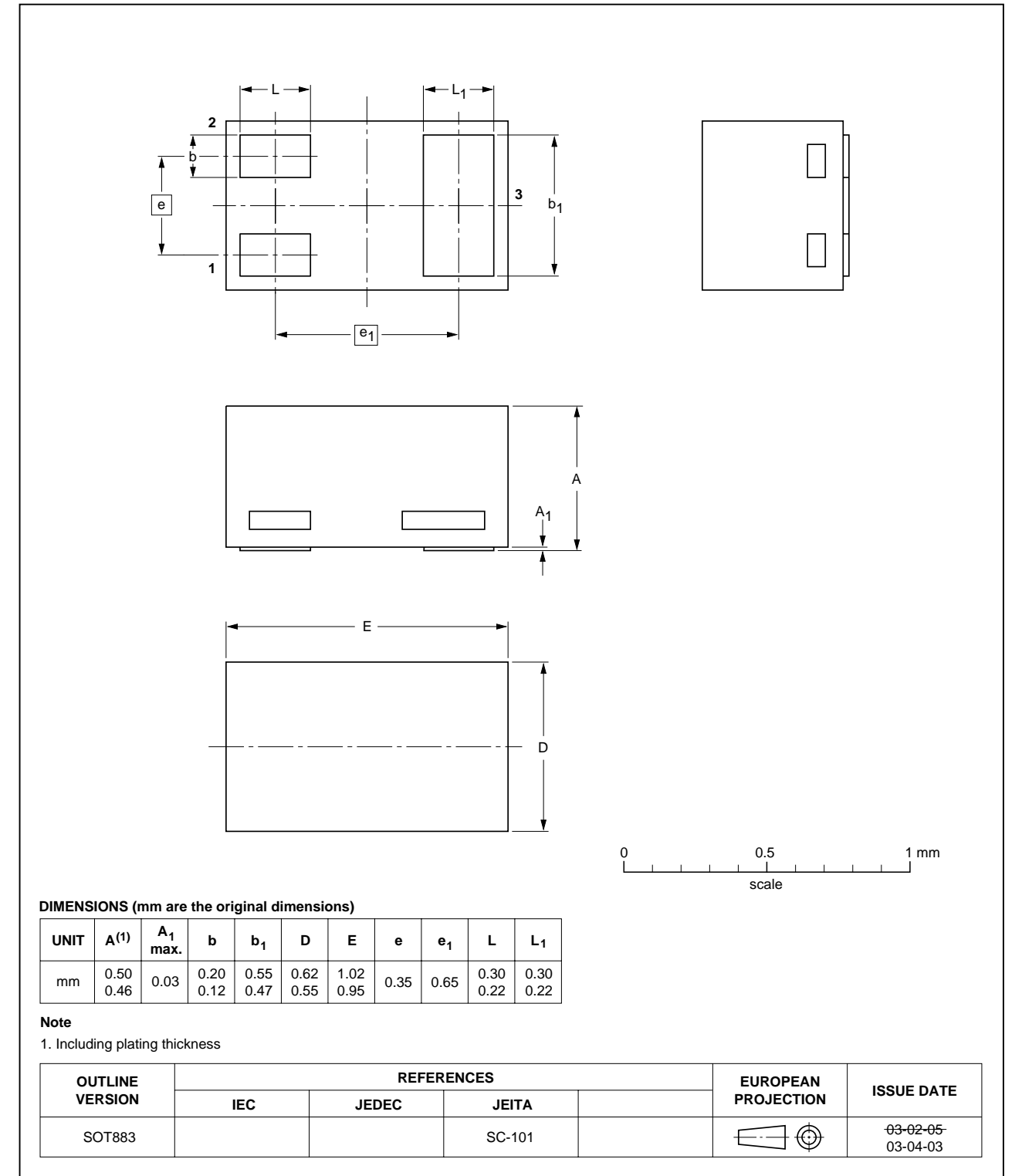


PNP resistor-equipped transistors;
R1 = 4.7 kΩ, R2 = 4.7 kΩ

PDTA143E series

Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

SOT883



PNP resistor-equipped transistors;
R1 = 4.7 k Ω , R2 = 4.7 k Ω

PDTA143E series

DATA SHEET STATUS

| DOCUMENT STATUS ⁽¹⁾ | PRODUCT STATUS ⁽²⁾ | DEFINITION |
|--------------------------------|-------------------------------|---|
| Objective data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary data sheet | Qualification | This document contains data from the preliminary specification. |
| Product data sheet | Production | This document contains the product specification. |

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2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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